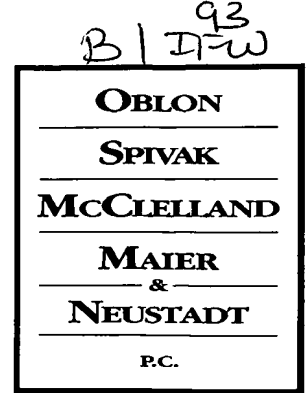




Docket No.: 213480US0

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313



ATTORNEYS AT LAW

RE: Application Serial No.: 09/942,626
Applicants: Sei TSUNODA, et al.
Filing Date: August 31, 2001
For: LOW DIELECTRIC CONSTANT MATERIAL
HAVING THERMAL RESISTANCE, INSULATION
FILM BETWEEN SEMICONDUCTOR LAYERS
USING THE SAME, AND SEMICONDUCTOR
DEVICE
Group Art Unit: 1751
Examiner: VIJAYAKUMAR, K.M.

SIR:

Attached hereto for filing are the following papers:

Amendment Under 37 CFR 1.312;
Copy of Form PTO-1449 as filed August 26, 2005

Our check in the amount of -0- is attached covering any required fees. In the event any variance exists between the amount enclosed and the Patent Office charges for filing the above-noted documents, including any fees required under 37 C.F.R. 1.136 for any necessary Extension of Time to make the filing of the attached documents timely, please charge or credit the difference to our Deposit Account No. 15-0030. Further, if these papers are not considered timely filed, then a petition is hereby made under 37 C.F.R. 1.136 for the necessary extension of time. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

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DOCKET NO: 213480US0

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
SEI TSUNODA, ET AL. : EXAMINER: VIJAYAKUMAR, K.M.
SERIAL NO: 09/942,626 :
FILED: AUGUST 31, 2001 : GROUP ART UNIT: 1751
FOR: LOW DIELECTRIC CONSTANT :
MATERIAL HAVING THERMAL
RESISTANCE, INSULATION FILM
BETWEEN SEMICONDUCTOR LAYERS
USING THE SAME, AND
SEMICONDUCTOR DEVICE

AMENDMENT UNDER 37 CFR 1.312

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Please amend the above-identified application pursuant to 37 CFR 1.312 as follows.

Amendments to the Claims are reflected in the listing of claims which begins on
page 2 of this paper.

Discussion of the Amendment begins on page 7 of this paper.

Remarks begin on page 8 of this paper.